



## Future Normal in Semiconductor

2025년 2월 13일(목), 09:00-10:45

Room E(에메랄드 II+III), 5층

### D. Thin Film Process Technology 분과

#### 005\_[TE1-D] Ferroelectrics

좌장: 최창환 교수(한양대학교), 전우진 교수(경희대학교)

<p>TE1-D-1 09:00-09:15</p>	<p><b>BEOL-Compatible and Robust Ferroelectricity in 5 nm-thick <math>\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2</math> film by Adopting TiN and Mo Alloy Electrode</b> Jaewook Lee, Yong Hyeon Cho, Hyeong Seok Choi, Hyun Woo Jeong, Hyojun Choi, and Min Hyuk Park Seoul National University</p>
<p>TE1-D-2 09:15-09:30</p>	<p><b>N-Terminated TiN Electrodes with (111) Texture for Low-Voltage Switching (0.8 V) in Ferroelectric <math>\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2</math> Capacitors</b> Geun Hyeong Park<sup>1</sup>, Yong Hyeon Cho<sup>1</sup>, Dong Hyun Lee<sup>1</sup>, Se Hyun Kim<sup>1</sup>, Ho Jun Kim<sup>2</sup>, and Min Hyuk Park<sup>1</sup> <sup>1</sup>Seoul National University, <sup>2</sup>Hanyang University</p>
<p>TE1-D-3 09:30-09:45</p>	<p><b>BEOL-Compatible Fabrication of Reliable FeFETs with Sub 10nm <math>\text{Hf}_x\text{Zr}_{1-x}\text{O}_2</math> Films</b> Geonwook Kim<sup>1</sup>, Hyunho Seok<sup>2</sup>, Sihoon Son<sup>2</sup>, Hyunbin Choi<sup>3</sup>, Jinhyoung Lee<sup>1</sup>, and Taesung Kim<sup>1,2,3</sup> <sup>1</sup>Department of Mechanical Engineering, Sungkyunkwan University, <sup>2</sup>SKKU Advance Institute of Nano Technology, <sup>3</sup>Department of Semiconductor Convergence Engineering, Sungkyunkwan University</p>
<p>TE1-D-4 09:45-10:00</p>	<p><b>Enhancing Memory Characteristics of MIFIS-FeFET: Effects of <math>\text{Si}_3\text{N}_4</math> Charge Injection Layer and Its Composition</b> Hyojin Ahn<sup>1</sup>, Hyunjin Lim<sup>1</sup>, Sangkuk Han<sup>1</sup>, Yehbeen Im<sup>1</sup>, Wonjae Choi<sup>2</sup>, Youngseo Na<sup>2</sup>, and Changhwan Choi<sup>1,2</sup> <sup>1</sup>Division of Materials Science and Engineering, Hanyang University, <sup>2</sup>Department of Semiconductor Engineering, Hanyang University</p>
<p>TE1-D-5 10:00-10:15</p>	<p><b>Understanding Domain switching Kinetics in Ferroelectric <math>\text{HfO}_2</math> : A Pseudo-Voigt and Machine Learning Approach</b> Yong Hyeon Cho, Geun Hyeong Park, Dong Hyun Lee, Hyun Woo Jung, Young Min Kim, Ho Won Jang, and Min Hyuk Park Department of Materials Science and Engineering, Inter-university Semiconductor Research Center, Seoul National University</p>



# 제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

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<p>초청 TE1-D-6 10:15-10:45</p>	<p>Parallel Synaptic Design of Ferroelectric Tunnel Junctions for Neuromorphic Computing Taehwan Moon Department of Intelligence Semiconductor Engineering, Ajou University</p>
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